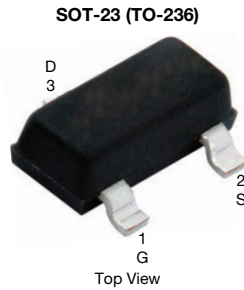


## P-Channel 20 V (D-S) MOSFET



Marking Code: P6

| PRODUCT SUMMARY                                     |        |
|---|--------|
| $V_{DS}$ (V)  | -20    |
| $R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = -4.5$ V | 0.061  |
| $R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = -2.5$ V | 0.080  |
| $R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = -1.8$ V | 0.110  |
| $R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = -1.5$ V | 0.165  |
| $Q_g$ typ. (nC)                                     | 7.6    |
| $I_D$ (A) <sup>a</sup>                              | -4.4   |
| Configuration                                       | Single |

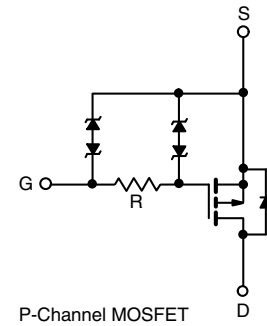
### FEATURES

- TrenchFET® power MOSFET
- 100%  $R_g$  tested
- Typical ESD performance 2000 V
- Built in ESD protection with Zener Diode
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
 COMPLIANT  
 HALOGEN  
 FREE

### APPLICATIONS

- Load switch for portable devices



| ORDERING INFORMATION            |                  |
|---------------------------------|------------------|
| Package                         | SOT-23           |
| Lead (Pb)-free and halogen-free | Si2377EDS-T1-GE3 |

| ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted) |                |               |                      |
|---|----------------|---------------|----------------------|
| PARAMETER   | SYMBOL         | LIMIT         | UNIT                 |
| Drain-source voltage  | $V_{DS}$       | -20           | V                    |
| Gate-source voltage   | $V_{GS}$       | $\pm 8$       |                      |
| Continuous drain current ( $T_J = 150$ °C)                        | $I_D$          | $T_C = 25$ °C | A                    |
|   |                | $T_C = 70$ °C |                      |
|   |                | $T_A = 25$ °C |                      |
|   |                | $T_A = 70$ °C |                      |
| Pulsed drain current  | $I_{DM}$       | -20           |                      |
| Continuous source-drain diode current                             | $I_S$          | $T_C = 25$ °C | -1.5                 |
|   |                | $T_A = 25$ °C | -1 <sup>b, c</sup>   |
| Maximum power dissipation   | $P_D$          | $T_C = 25$ °C | 1.8                  |
|   |                | $T_C = 70$ °C | 1.1                  |
|   |                | $T_A = 25$ °C | 1.25 <sup>b, c</sup> |
|   |                | $T_A = 70$ °C | 0.8 <sup>b, c</sup>  |
| Operating junction and storage temperature range                  | $T_J, T_{stg}$ | -55 to +150   | °C                   |
| Soldering recommendations (peak temperature) <sup>d, e</sup>      |                | 260           |                      |

| THERMAL RESISTANCE RATINGS                  |              |            |         |         |      |
|---|--------------|------------|---------|---------|------|
| PARAMETER                                   |              | SYMBOL     | TYPICAL | MAXIMUM | UNIT |
| Maximum junction-to-ambient <sup>b, d</sup> | $t \leq 5$ s | $R_{thJA}$ | 80      | 100     | °C/W |
| Maximum junction-to-foot (drain)            | Steady state | $R_{thJF}$ | 55      | 70      |      |

### Notes

- $T_C = 25$  °C
- Surface mounted on 1" x 1" FR4 board
- $t = 5$  s
- Maximum under steady state conditions is 130 °C/W



| <b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted) |                         |   |      |       |           |                      |
|--|-------------------------|---|------|-------|-----------|----------------------|
| PARAMETER  | SYMBOL                  | TEST CONDITIONS   | MIN. | TYP.  | MAX.      | UNIT                 |
| <b>Static</b>  |                         |   |      |       |           |                      |
| Drain-source breakdown voltage   | $V_{DS}$                | $V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$  | -20  | -     | -         | V                    |
| $V_{DS}$ temperature coefficient   | $\Delta V_{DS}/T_J$     | $I_D = -250\text{ }\mu\text{A}$   | -    | -13   | -         | mV/ $^\circ\text{C}$ |
| $V_{GS(th)}$ temperature coefficient   | $\Delta V_{GS(th)}/T_J$ |   | -    | 2.5   | -         |                      |
| Gate-source threshold voltage  | $V_{GS(th)}$            | $V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$  | -0.4 | -     | -1        | V                    |
| Gate-source leakage  | $I_{GSS}$               | $V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$  | -    | -     | $\pm 6$   | $\mu\text{A}$        |
|  |                         | $V_{DS} = 0\text{ V}, V_{GS} = \pm 4.5\text{ V}$  | -    | -     | $\pm 0.5$ |                      |
| Zero gate voltage drain current  | $I_{DSS}$               | $V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$  | -    | -     | -1        |                      |
|  |                         | $V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$  | -    | -     | -10       |                      |
| On-state drain current <sup>a</sup>  | $I_{D(on)}$             | $V_{DS} \leq -5\text{ V}, V_{GS} = -4.5\text{ V}$   | -15  | -     | -         | A                    |
| Drain-source on-state resistance <sup>a</sup>                                      | $R_{DS(on)}$            | $V_{GS} = -4.5\text{ V}, I_D = -3.2\text{ A}$   | -    | 0.050 | 0.061     | $\Omega$             |
|  |                         | $V_{GS} = -2.5\text{ V}, I_D = -2.8\text{ A}$   | -    | 0.065 | 0.080     |                      |
|  |                         | $V_{GS} = -1.8\text{ V}, I_D = -1.5\text{ A}$   | -    | 0.090 | 0.110     |                      |
|  |                         | $V_{GS} = -1.5\text{ V}, I_D = -0.5\text{ A}$   | -    | 0.110 | 0.165     |                      |
| Forward transconductance <sup>a</sup>  | $g_{fs}$                | $V_{DS} = -10\text{ V}, I_D = -3.2\text{ A}$  | -    | 12    | -         | S                    |
| <b>Dynamic <sup>b</sup></b>  |                         |   |      |       |           |                      |
| Total gate charge  | $Q_g$                   | $V_{DS} = -10\text{ V}, V_{GS} = -8\text{ V}, I_D = -5.3\text{ A}$  | -    | 14    | 21        | nC                   |
|  |                         | $V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -5.3\text{ A}$  | -    | 7.6   | 12        |                      |
|  |                         |   | -    | 0.8   | -         |                      |
| Gate-source charge   | $Q_{gs}$                | $V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -5.3\text{ A}$  | -    | 3.1   | -         | nC                   |
| Gate-drain charge  | $Q_{gd}$                |   | -    | -     | -         |                      |
| Gate resistance  | $R_g$                   | $f = 1\text{ MHz}$  | 0.4  | 2     | 4         | k $\Omega$           |
| Turn-on delay time   | $t_{d(on)}$             | $V_{DD} = -10\text{ V}, R_L = 2.3\text{ }\Omega$<br>$I_D \cong -4.3\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$ | -    | 0.2   | 0.3       | $\mu\text{s}$        |
| Rise time  | $t_r$                   |   | -    | 1     | 1.5       |                      |
| Turn-off delay time  | $t_{d(off)}$            |   | -    | 4     | 6         |                      |
| Fall time  | $t_f$                   |   | -    | 2     | 3         |                      |
| Turn-on delay time   | $t_{d(on)}$             | $V_{DD} = -10\text{ V}, R_L = 2.3\text{ }\Omega$<br>$I_D \cong -4.3\text{ A}, V_{GEN} = -8\text{ V}, R_g = 1\text{ }\Omega$   | -    | 0.09  | 0.14      |                      |
| Rise time  | $t_r$                   |   | -    | 0.4   | 0.6       |                      |
| Turn-off delay time  | $t_{d(off)}$            |   | -    | 5.2   | 7.8       |                      |
| Fall time  | $t_f$                   |   | -    | 2.3   | 3.5       |                      |
| <b>Drain-Source Body Diode Characteristics</b>                                     |                         |   |      |       |           |                      |
| Continuous source-drain diode current  | $I_S$                   | $T_C = 25\text{ }^\circ\text{C}$  | -    | -     | -1.5      | A                    |
| Pulse diode forward current  | $I_{SM}$                |   | -    | -     | -20       |                      |
| Body diode voltage   | $V_{SD}$                | $I_S = -3\text{ A}, V_{GS} = 0\text{ V}$  | -    | -0.8  | -1.2      | V                    |
| Body diode reverse recovery time   | $t_{rr}$                | $I_F = -3\text{ A}, di/dt = 100\text{ A}/\mu\text{s},$<br>$T_J = 25\text{ }^\circ\text{C}$                                    | -    | 30    | 60        | ns                   |
| Body diode reverse recovery charge   | $Q_{rr}$                |   | -    | 20    | 40        | nC                   |
| Reverse recovery fall time   | $t_a$                   |   | -    | 13    | -         | ns                   |
| Reverse recovery rise time   | $t_b$                   |   | -    | 17    | -         |                      |

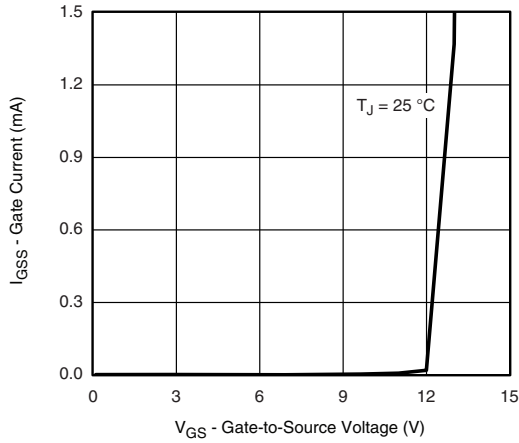
**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$
- b. Guaranteed by design, not subject to production testing

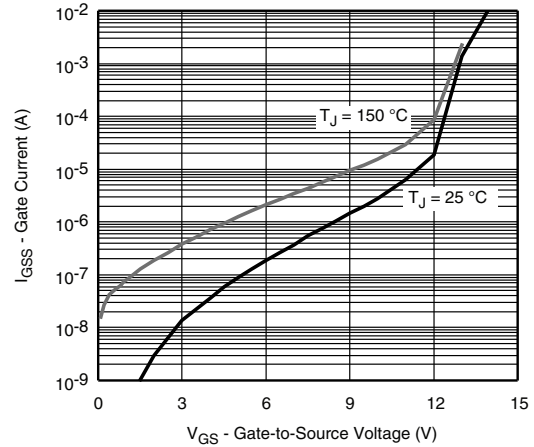
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



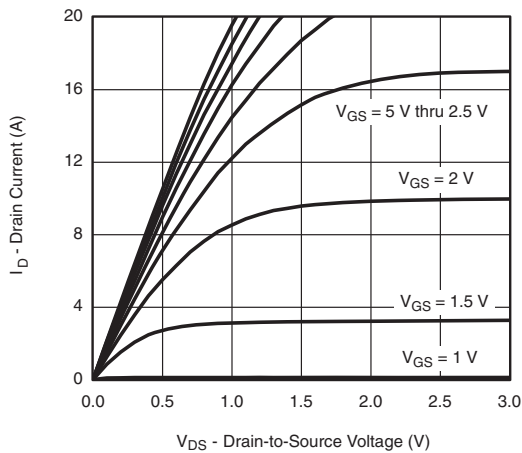
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



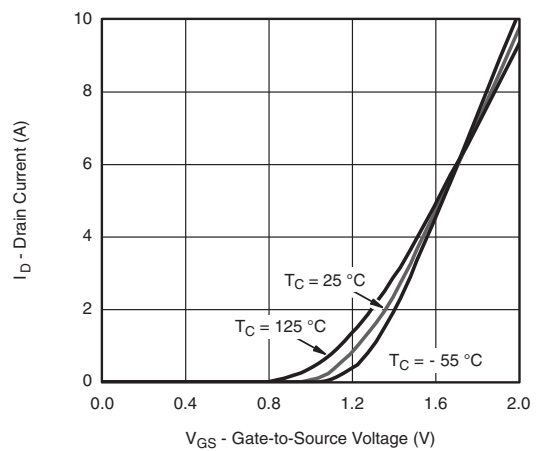
Gate Current vs. Gate-Source Voltage



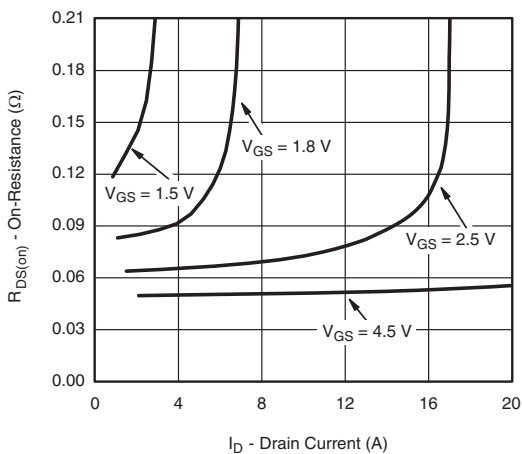
Gate Current vs. Gate-Source Voltage



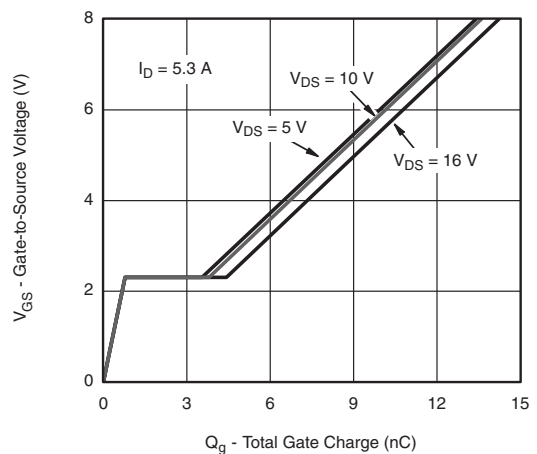
Output Characteristics



Transfer Characteristics



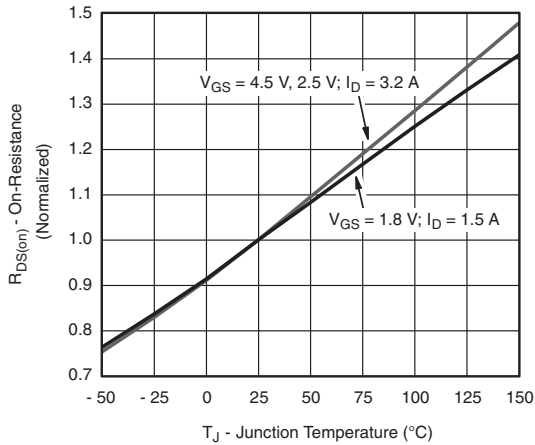
On-Resistance vs. Drain Current



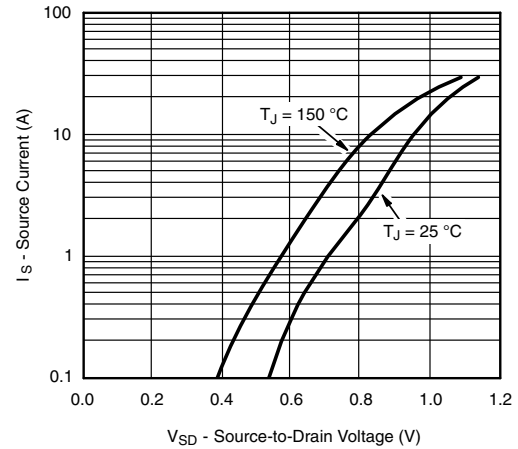
Gate Charge



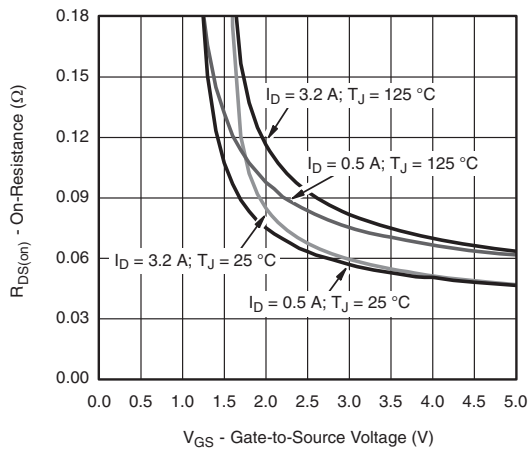
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



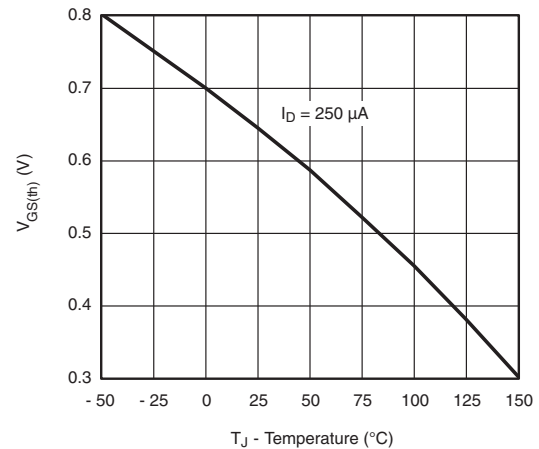
**On-Resistance vs. Junction Temperature**



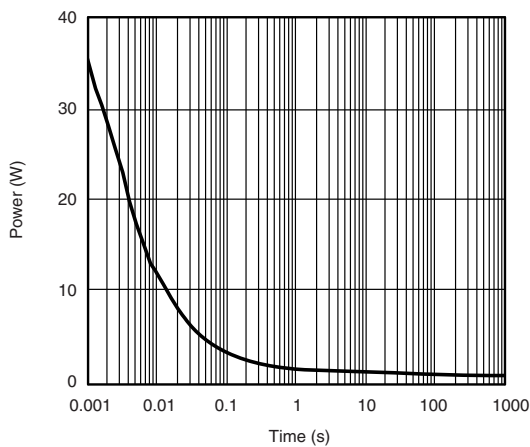
**Source-Drain Diode Forward Voltage**



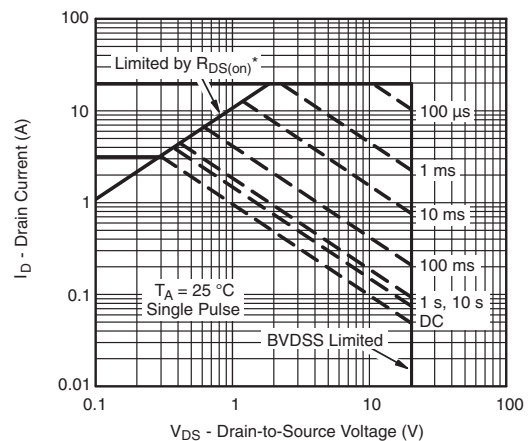
**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**



**Single Pulse Power, Junction-to-Ambient**

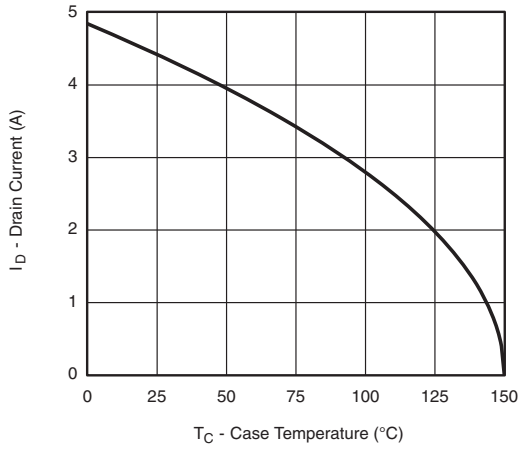


\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

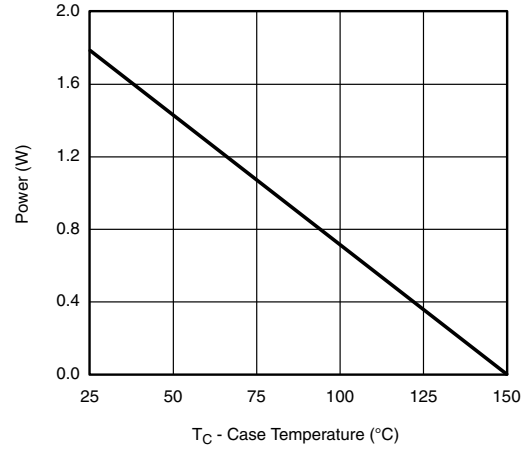
**Safe Operating Area, Junction-to-Ambient**



**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Current Derating <sup>a</sup>**



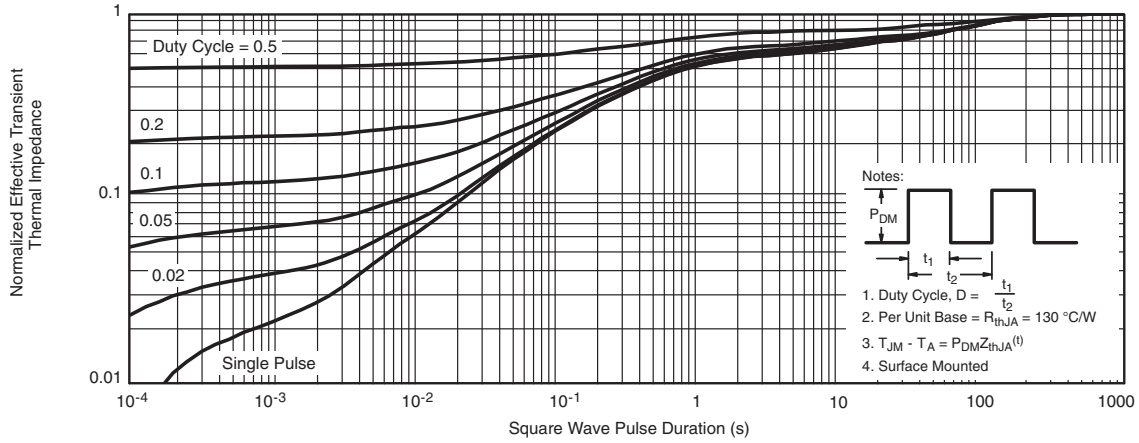
**Power Derating**

**Note**

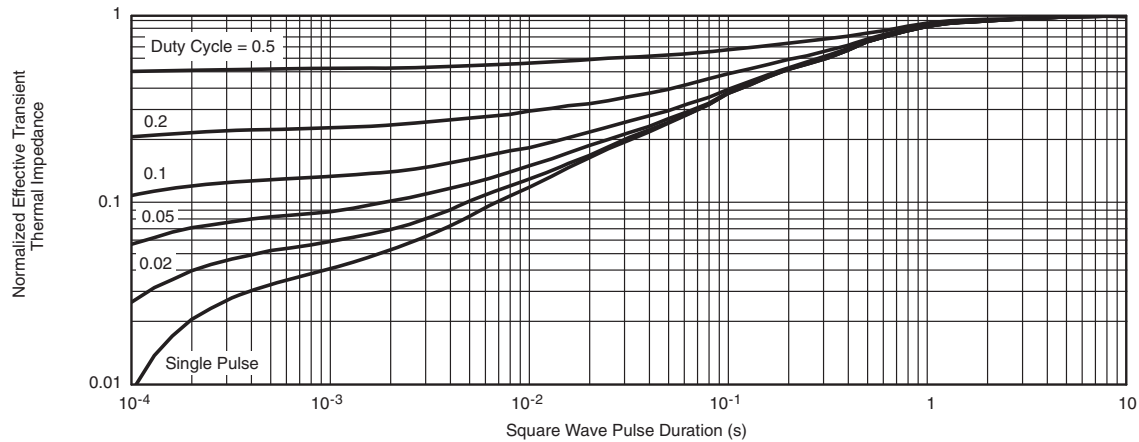
- a. The power dissipation  $P_D$  is based on  $T_J \text{ max.} = 150 \text{ }^\circ\text{C}$ , using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



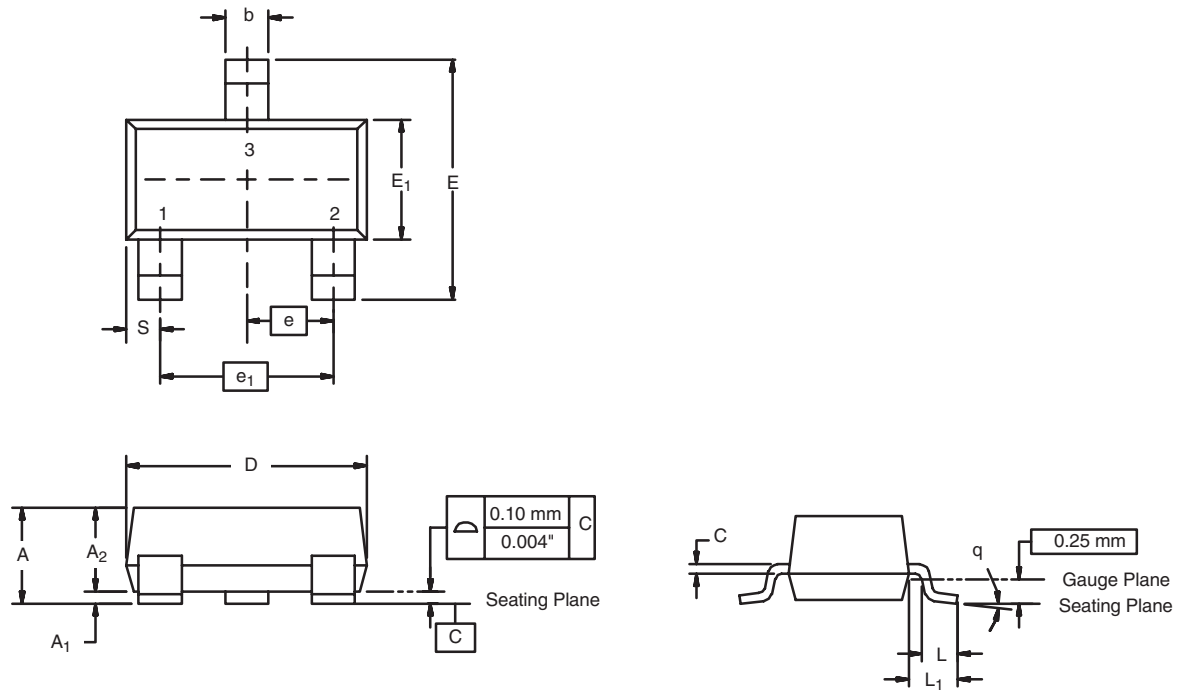
**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Foot**

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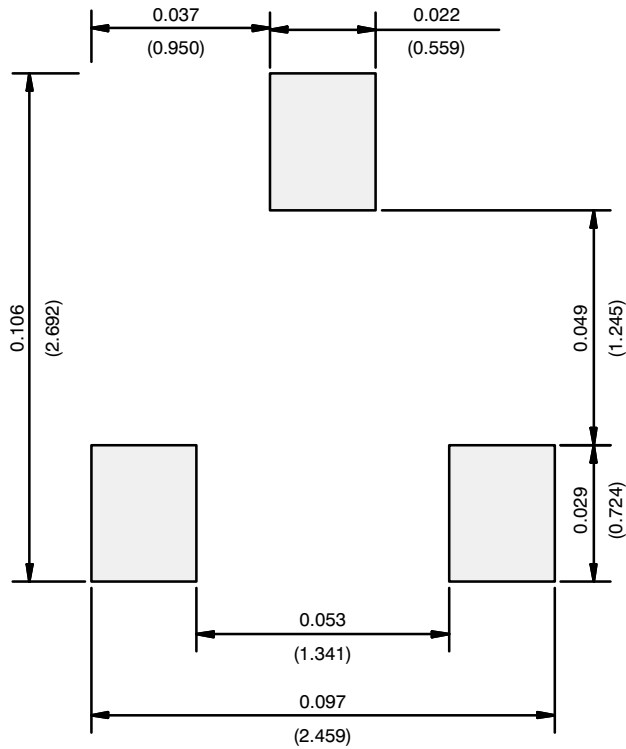
## SOT-23 (TO-236): 3-LEAD



| Dim            | MILLIMETERS |      | INCHES     |       |
|----------------|-------------|------|------------|-------|
|                | Min         | Max  | Min        | Max   |
| A              | 0.89        | 1.12 | 0.035      | 0.044 |
| A <sub>1</sub> | 0.01        | 0.10 | 0.0004     | 0.004 |
| A <sub>2</sub> | 0.88        | 1.02 | 0.0346     | 0.040 |
| b              | 0.35        | 0.50 | 0.014      | 0.020 |
| c              | 0.085       | 0.18 | 0.003      | 0.007 |
| D              | 2.80        | 3.04 | 0.110      | 0.120 |
| E              | 2.10        | 2.64 | 0.083      | 0.104 |
| E <sub>1</sub> | 1.20        | 1.40 | 0.047      | 0.055 |
| e              | 0.95 BSC    |      | 0.0374 Ref |       |
| e <sub>1</sub> | 1.90 BSC    |      | 0.0748 Ref |       |
| L              | 0.40        | 0.60 | 0.016      | 0.024 |
| L <sub>1</sub> | 0.64 Ref    |      | 0.025 Ref  |       |
| S              | 0.50 Ref    |      | 0.020 Ref  |       |
| q              | 3°          | 8°   | 3°         | 8°    |

ECN: S-03946-Rev. K, 09-Jul-01  
 DWG: 5479

## RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads  
Dimensions in Inches/(mm)

[Return to Index](#)





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